

Description

TECHNICAL FIELD

[0001] The present disclosure relates to the field of liquid crystal display, in particular, to a gate line driving method and apparatus, a shifting register, and a display device.

BACKGROUND

[0002] The pixel array for a liquid crystal display includes a plurality of gate lines and a plurality of data lines which are interlaced each other, with a gate line corresponding to a row of the pixel array and a data line corresponding to a column of the pixel array. The driving for the gate lines can be implemented by an integral driving circuit attached. With the development of the process on the amorphous silicon film in recent years, it is possible to integrate the gate line driving circuit into the substrate of the Thin Film Transistor (TFT) arrays to construct a shifting register so as to drive the gate line.

[0003] The gate line driving apparatus constituted by a plurality of shifting registers provide the plurality of gate lines in the pixel array with the switching signals so that the plurality of gate lines are controlled to be switched on in sequence, and the pixel electrodes in the corresponding row in the pixel array are charged from the data lines to form the gray voltages required by the respective gray levels to display an image, and thus each frame of the image can be displayed.

[0004] It is required that, in each of the shifting registers, the thin film transistors are turned on and/or off to realize the switching-on or switching-off of the corresponding gate line. However, during the actual operation, the thin film transistors fail to be turned on normally after a period of time due to the occurrence of the threshold voltage shifting (here referring to positive shifting, i.e., the increase of the threshold voltage).

[0005] The increase of the threshold voltage for turning on the thin film transistor relates to the voltage applied between the source and the gate thereof. The higher the voltage applied between the source and the gate and the longer the time for the voltage being applied is, the more the threshold voltage for turning on the thin film transistor increases. Therefore, if a voltage is applied to a thin film transistor all the time, the threshold voltage shifting would increase all along, which results in the failure to turn on the thin film transistor normally, and finally causes malfunction of the shifting register circuit.

SUMMARY

[0006] The embodiments of the disclosure provide a gate line driving method, a shifting register, a gate line driving apparatus and a display device, and can improve the stability of the shifting register in operation.

[0007] According to an embodiment of the disclosure,

a gate line driving method is provided, and the method comprises the steps of:

[0008] decreasing the threshold voltage shifting of a thin film transistor in a shifting register corresponding to a gate line;

[0009] applying a voltage to a gate of the thin film transistor in the shifting register to turn on the thin film transistor, so that the gate line is provided with a line scan signal to drive the gate line to be switched on.

[0010] According to an embodiment of the disclosure, a shifting register is provided, and the shifting register includes:

a first Thin Film Transistor TFT, having a gate and a source connected together and further connected to a trigger signal terminal at the present stage, and a drain connected to a first node as a pull-up node; a second TFT, having a gate connected to a first node, a source connected to a clock signal terminal, and a drain connected to an output terminal at the present stage;

a capacitor, being connected between the first node and the output terminal at the present stage;

a resetting module, being connected between a second node as a pull-down node, the clock signal terminal and a low level signal terminal, for applying a low level to the drain and the gate of the second TFT after the output of the present stage is completed; and

a feedback receiving module, being connected between the first node, the low level signal terminal and the output terminal at the present stage, and further being connected to a feedback signal terminal, for receiving a feedback signal from the next stage to pull down the first node and the output terminal at the present stage.

According to an embodiment of the disclosure, a gate line driving apparatus comprising a plurality of the shifting register as mentioned above connected in series, is provided.

[0011] In addition, according to an embodiment of the disclosure, a display device, including a pixel array and the gate line driving apparatus as mention above, is provided.

[0012] It tends to form and accumulate electrons on the gate insulation layer of a thin film transistor if a voltage is applied to a gate of the thin film transistor for a long time, and thus it causes the threshold voltage of the thin film transistor to shift. In the gate line driving method, the shifting register, the gate line driving apparatus and the display device according to the embodiments of the disclosure, by applying a high level to the source of the TFT and a low level to the gate thereof, according to the principle of the tunnelling effect and the quantum mechanics, the electrons formed and accumulated on the gate insulation layer of the TFT can pass the potential barrier and arrive at the source of the TFT, and thus it decreases the

threshold voltage shifting of the TFT in the shifting register corresponding to each gate line, and finally it enables the shifting register circuit to operate normally, improving the stability of the shifting register in operation and extending the lifespan of the shifting register.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013]

Fig.1 is a schematic diagram of a gate line driving method according to an embodiment of the disclosure;

Fig. 2 is a schematic diagram of a shifting register according to an embodiment of the disclosure;

Fig. 3 is a schematic diagram of a specific embodiment of the shifting register of the disclosure;

Fig. 4 is a timing control chart for the shifting register shown in Fig. 3;

Fig. 5 is a schematic diagram of the shifting register shown in Fig. 3 in operation during t1 phase;

Fig. 6 is a schematic diagram of the shifting register shown in Fig. 3 in operation during t2 phase;

Fig. 7 is a schematic diagram of the shifting register shown in Fig. 3 in operation during t3 phase;

Fig. 8 is a schematic diagram of the shifting register shown in Fig. 3 in operation during t4 phase; and

Fig. 9 is a schematic diagram of a gate line driving apparatus according to an embodiment of the disclosure.

DETAILED DESCRIPTION

[0014] Hereinafter, a gate line driving method, a shifting register, a gate line driving apparatus and a display device in accordance with the disclosure are described in detail with reference to the drawings.

[0015] It should be appreciated that all the embodiments as described are only parts of embodiments rather than all the possible embodiments of the disclosure. All the other embodiments, which are obtained by those skilled in the art based on the embodiments proposed in the disclosure without paying any inventive labor, should belong to the scope as claimed by the disclosure.

[0016] It should be noted that the terms of "source" and "drain" defined in the specification and claims are interchangeable, and the direction of an arrow only represents the conduction of the transistor instead of the direction of the conduction.

[0017] As shown in Fig. 1, it is the schematic diagram of a gate line driving method of an embodiment of the disclosure. The gate line driving method comprises:

[0018] in step 11, decreasing the threshold voltage shifting of a thin film transistor in a shifting register corresponding to a row gate line;

[0019] in step 12, applying a voltage to a gate of the thin film transistor in the shifting register to turn on the thin film transistor, so that the gate line is provided with

a line scan signal to drive the gate line to be switched on.

[0020] It tends to form and accumulate electrons in the gate insulation layer of a thin film transistor if a voltage is applied to the gate of the thin film transistor all the time, and thus causes the threshold voltage of the thin film transistor to shift. According to the gate line driving method as provided in the embodiments of the disclosure, it enables the shifting register circuit to operate normally by decreasing the threshold voltage shifting of the thin film transistor in the shifting register corresponding to each gate line, improving the stability of the shifting register in operation and extending the lifespan of the shifting register.

[0021] As known from above, the threshold voltage shifting of the thin film transistor generally results from the electrons formed and accumulated on the gate insulation layer of the thin film transistor. The Step 11 mentioned above, i.e., decreasing the threshold voltage shifting of the thin film transistor in the shifting register corresponding to a gate line can further comprise;

[0022] in step 111, allowing the electrons accumulated on the gate insulation layer of the thin film transistor to arrive at the source thereof, to decrease the threshold voltage shifting of the thin film transistor.

[0023] It should be noted that other factors can also result in the threshold voltage shifting in addition to the formation and accumulation of the electrons on the gate insulation layer of the thin film transistor, such as accumulation of the electrons on the passivation layer. Therefore, the step for decreasing the threshold voltage shifting of the thin film transistor in the shifting register corresponding to each gate line as proposed in the embodiment, can not only comprise the above step 111, but also comprise other steps, such as the step for allowing the electrons accumulated on the passivation layer to arrive at the source of the thin film transistor and the like.

[0024] the above step 111, i.e., allowing the electrons accumulated on the gate insulation layer of the TFT to arrive at the source thereof, comprises the step of: applying a high level to the source of the TFT and a low level to the gate thereof, so that the electrons accumulated on the gate insulation layer of the TFT can arrive at the source thereof.

[0025] According to the principle of the tunnelling effect and the quantum mechanics, subsequent to the application of the high level to the source of the TFT and the low level to the gate thereof, the electrons formed and accumulated on the gate insulation layer of the TFT can pass the potential barrier and arrive at the source of the TFT, and thus decreasing the threshold voltage shifting of the TFT due to the accumulation of the electrons on the gate insulation layer thereof.

[0026] Hereinafter, a shifting register is designed and manufactured according to the gate line driving method, and the shifting register has a high stability in operation. For example, as shown in Fig.2, the shifting register according to the embodiment includes three TFTs, a storage capacitor, a resetting module, a feedback receiving

module, and corresponding I/O terminals. In particular, the shifting register includes:

[0027] a first TFT M1, having a gate and a source connected together and further connected to a trigger signal terminal Input(n) at the present stage (i.e., at the n^{th} stage), and a drain connected to a first node PU as a pull-up node, for controlling the shifting register to start operation upon receiving a high level signal sent from the trigger signal terminal Input(n), wherein the trigger signal terminal Input(n) receives a high level signal when an output terminal Output(n-1) of the shifting register at the previous stage (i.e., the shifting register at the $(n-1)^{\text{th}}$ stage) outputs a high level;

[0028] a second thin film transistor M2, having a gate connected to the first node PU, a source connected to a clock signal terminal, and a drain connected to an output terminal Output(n) at the present stage, for providing a high level output for the output terminal Output(n) to drive the gate line corresponding to the shifting register at the present stage (i.e., the shifting register at the n^{th} stage) to be switched on;

[0029] a third TFT M3, having a gate connected to the first node PU, a source connected to the clock signal terminal, and a drain connected to a trigger signal terminal Input(n+1) for the next stage (i.e., the $(n+1)^{\text{th}}$ stage), for providing a trigger signal for the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage) to control the same to start operation;

[0030] a capacitor C1, being connected between the first node PU and the output terminal Output(n) at the present stage;

[0031] a resetting module 1, being connected between a second node PL as a pull-down node, the clock signal terminal and a low level signal terminal Vss, for applying a low level to the drain and the gate of the second TFT M2 after the output of the present stage is completed; and

[0032] a feedback receiving module 2, being connected between the first node PU, the low level signal terminal Vss and the output terminal Output(n) at the present stage, and being further connected to the feedback signal terminal Reset(n+1), for receiving a feedback signal from the next stage to pull down the levels at the first node PU and the output terminal Output(n) at the present stage, wherein the feedback signal terminal Reset(n+1) receives a high level signal when the output terminal Output(n+1) of the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage) outputs a high level; and the feedback signal terminal Reset(n+1) can be either connected to the output terminal Output(n+1) of the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage), or connected to a trigger signal terminal Input(n+2) of the shifting register at the stage subsequent to the next stage of the present stage (i.e., the shifting register at the $(n+2)^{\text{th}}$ stage).

[0033] It should be noted that although the shifting register in Fig.2 includes three TFTs, the embodiments of the disclosure are not limited thereto. For example, in a shifting register according to an embodiment of the dis-

closure, the third TFT M3 can be excluded, and the output terminal Output(n) at the present stage connected to the drain of the second TFT M2 can serve to be connected to the trigger signal terminal Input(n+1) for the next stage.

[0034] Thus, a shifting register according to another embodiment of the disclosure includes two TFTs, a storage capacitor, a resetting module, a feedback receiving module and corresponding I/O terminals. In particular, the shifting register includes:

[0035] a first TFT M1, having a gate and a source connected together and further connected to a trigger signal terminal Input(n) at the present stage, and a drain connected to a first node PU as a pull-up node, for controlling the shifting register to start operation upon receiving a high level signal sent from the trigger signal terminal Input(n) at the present stage, wherein the trigger signal terminal Input(n) receives a high level signal when an output terminal Output(n-1) of the shifting register at the previous stage (i.e., the shifting register at the $(n-1)^{\text{th}}$ stage) outputs a high level;

[0036] a second TFT M2, having a gate connected to the first node PU, a source connected to a clock signal terminal, and a drain connected to an output terminal Output(n) at the present stage and a trigger signal terminal Input(n+1) for the next stage, for providing a high level output for the output terminal Output(n) at the present stage so as to drive the gate line corresponding to the shifting register at the present stage (i.e., the shifting register at the n^{th} stage) to be switched on, and to provide a trigger signal for the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage) to control the same to start operation;

[0037] a capacitor C1, being connected between the first node PU and the output terminal Output(n) at the present stage;

[0038] a resetting module 1, being connected between a second node PL as a pull-down node, the clock signal terminal and a low level signal terminal Vss, for applying a low level to the drain and the gate of the second TFT M2 after the output of the present stage is completed; and

[0039] a feedback receiving module 2, being connected between the first node PU, the low level signal terminal Vss and the output terminal Output(n) at the present stage, and being further connected to a feedback signal terminal Reset(n+1), for receiving a feedback signal from the next stage to pull down the levels at the first node PU and the output terminal Output(n) of the present stage, wherein the feedback signal terminal Reset(n+1) receives a high level signal when the output terminal Output(n+1) of the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage) outputs a high level; and the feedback signal terminal Reset(n+1) can be connected to the output terminal Output(n+1) of the shifting register at the next stage (i.e., the shifting register at the $(n+1)^{\text{th}}$ stage), or the feedback signal terminal Reset(n+1) can be connected to another TFT (e.g., the TFT M3 in Fig.2) which is added to the shifting register at the next stage (i.e., the shifting register at the $(n+2)^{\text{th}}$ stage)

for providing a feedback signal.

[0040] It tends to form and accumulate electrons in the gate insulation layer of a thin film transistor if a voltage is applied to the thin film transistor all the time, and thus causes the threshold voltage of the thin film transistor to shift. According to the shifting register provided in the embodiment of the disclosure, based on the principle of the tunnelling effect and the quantum mechanics, by applying a high level to the source of the TFT and a low level to the gate thereof, the electrons formed and accumulated on the gate insulation layer of the TFT can pass the potential barrier and arrive at the source thereof to decrease the threshold voltage shifting of the TFT in the shifting register corresponding to each gate line, and thus it allows the shifting register circuit to operate normally, improving the stability of the shifting register in operation and extending the lifespan of the shifting register. It should be illustrated that, the threshold voltage shifting occurs in the individual TFTs in the shifting register due to the formation and accumulation of the electrons on the gate insulation layer of the corresponding TFTs, so the corresponding TFTs in the shifting register can be provided with a resetting module 1, for applying a high level to the source of the TFT and a low level to the gate thereof after the output of the present stage of the shifting register is completed, such that the electrons at the gate insulation layer of the TFT can arrive at the source thereof to decrease the threshold voltage shifting of the TFT. Since in the shifting register, the second TFT M2 can switch on the connection between the clock signal terminal and the output terminal of the present stage to allow the gate line corresponding to the shifting register to be switched on, the second TFT M2 plays a very important role in the shifting register. Once the second TFT M2 fails to be turned on normally due to the threshold voltage shifting, the quality of the display will be affected. In addition, the operation current in the second TFT M2 is large in general, which tends to cause the threshold voltage shifting. Therefore, taking the second TFT M2 as an example in the embodiment, it describes how to decrease the threshold voltage shifting of the TFT by use of the resetting module 1. It should be appreciated that the description is only for illustration and not for limitation.

[0041] As shown in Fig. 3, it is a schematic diagram of a shifting register of a specific embodiment of the disclosure. It can be known from the Fig. 3, the shifting register includes fourteen TFTs, a storage capacitor, and corresponding I/O terminals. The fourteen TFTs are as follows respectively: a first TFT M1, a second TFT M2, a third TFT M3, a fourth TFT M4, a fifth TFT M5, a sixth TFT M6, a seventh TFT M7, an eighth TFT M8, a ninth TFT M9, a tenth TFT M10, a first resetting TFT T1, a second resetting TFT T2, a third resetting TFT T3, and a fourth resetting TFT T4. The storage capacitor is shown as a capacitor C1. The I/O terminals includes: a trigger signal terminal Input(n) for receiving a trigger signal from the shifting register at the previous stage; an output terminal Output(n) for outputting a level signal for the shifting reg-

ister at the present stage; a trigger signal terminal Input(n+1) for sending a trigger signal to the shifting register at the next stage; a feedback signal terminal Reset(n+1) for receiving a feedback signal from the shifting register at the next stage; a low level signal terminal Vss, and clock signal terminals, wherein the clock signal terminals include a first clock signal terminal CLK and a second clock signal terminal CLKB, and a clock signal at the first clock signal terminal CLK and that at the second clock signal terminal

[0042] CLKB have the same frequency and duty cycle, but only differ in phase by 180°.

[0043] In particular, the first TFT M1 has a gate and a source connected together and further connected to the trigger signal terminal Input(n) at the present stage, and a drain connected to a first node PU as a pull-up node; the second TFT M2 has a gate connected to the first node PU, a source connected to the first clock signal terminal CLK, and a drain connected to the output terminal Output(n) at the present stage; the third TFT M3 has a gate connected to the first node PU, a source connected to the first clock signal terminal CLK, and a drain connected to the trigger signal terminal Input(n+1) for the next stage; the fourth TFT M4 has a gate connected to the feedback signal terminal Reset(n+1), a source connected to the output terminal Output(n) at the present stage, and a drain connected to the low level signal terminal Vss; the fifth TFT M5 has a gate connected to the feedback signal terminal Reset(n+1), a source connected to the first node PU, and a drain connected to the low level signal terminal Vss; the sixth TFT M6 has a gate connected to the second clock signal terminal CLKB, a source connected to a second node PL, and a drain connected to the low level signal terminal Vss; the seventh TFT M7 has a gate connected to the second clock signal terminal CLKB, a source connected to the trigger signal terminal Input(n) at the present stage, and a drain connected to the first node PU; the eighth TFT M8 has a gate connected to the first clock signal terminal CLK, a source connected to the first node PU, and a drain connected to the second node PL; the ninth TFT M9 has a gate connected to a drain of the fourth resetting TFT T4 in the resetting module 1, a source connected to the first node PU, and a drain connected to the low level signal terminal Vss; the tenth TFT M10 has a gate connected to the drain of the fourth resetting TFT T4 in the resetting module 1, a source connected to the output terminal Output(n) at the present stage, and a drain connected to the low level signal terminal Vss. The first resetting TFT T1 has a gate connected to the second node PL, a source connected to a drain of the third resetting TFT M3, and a drain connected to the low level signal terminal Vss; the second resetting TFT T2 has a gate connected to the second node PL, a source connected to the drain of the fourth resetting TFT T4, and a drain connected to the low level signal terminal Vss; the third resetting TFT T3 has a gate and a source connected to the first clock signal terminal CLK, a drain connected to the source of the first resetting TFT T1; the

fourth resetting TFT T4 has a gate connected to the drain of the third resetting TFT T3, a source connected to the first clock signal terminal CLK, and a drain connected to the source of the second resetting TFT T2. The storage capacitor is connected between the first node PU and the output terminal Output(n) at the present stage.

[0044] The first resetting TFT T1, the second resetting TFT T2, the third resetting TFT T3 and the fourth resetting TFT T4 have the same structures as those of the first TFT M1 to the tenth TFT M10. The first resetting TFT T1, the second resetting TFT T2, the third resetting TFT T3 and the fourth resetting TFT T4 constitute the resetting module 1 of the present embodiment, and they are differentiated from the first TFT M1 to the tenth TFT M10 in the names.

[0045] As described above, the first resetting TFT T1, the second resetting TFT T2, the third resetting TFT T3 and the fourth resetting TFT T4 constitute the resetting module 1 of the present embodiment, and the resetting module 1 is used for applying a high level to the source of the second TFT T2 and a low level to the gate thereof after the output of the present stage is completed, and thus according to the principle of the tunneling effect and the quantum mechanics, the electrons formed and accumulated at the gate insulation layer of the second TFT M2 can pass the potential barrier and arrive at the source of the second TFT M2 to decrease the threshold voltage shifting of the second TFT M2 in the shifting register corresponding to each of the gate lines, and finally it allows the shifting register circuit to operate normally, improving the stability of the shifting register in operation and extending the lifespan of the shifting register.

[0046] The fourth TFT M4 and the fifth TFT M5 constitute the feedback receiving module 2. The feedback receiving module 2 keeps the output terminal Output(n) at the present stage and the first node PU as the pull-up node at a low level when the shifting register at the present stage is not in operation and the shifting register at the next stage is in operation, so as to avoid the occurrence of the following case: the output terminal Output(n) at the present stage changes to a high level under the influence of the other interference signals, and thus causes the gate line under the control thereof to be switched on, finally resulting in the switching-on of the gate line in error. The fourth TFT M4 keeps the output terminal Output(n) at the present stage at a low level under the action of the feedback signal terminal Reset(n+1), and the fifth TFT M5 keeps the first node PU at a low level under the action of the feedback signal terminal Reset(n+1), so as to prevent the second TFT M2 from turning on in error.

[0047] As known from Fig. 3, the shifting register further includes the sixth TFT M6. The sixth TFT M6, when the shifting register at the present stage is not in operation, pulls down the second node PL as a pull-down node by receiving a high level signal at the second clock signal terminal CLKB, so as to avoid the occurrence of the following case: the output terminal Output(n) of the present

stage changes to a high level under the influence of the other interference signals, and thus causes the gate line under the control thereof to be switched on, finally resulting in the switching-on of the gate line in error.

5 **[0048]** The shifting register further includes the seventh TFT M7. The seventh TFT M7 accelerates the charging process of the storage capacitor C1 when the trigger signal terminal Input(n) at the present stage is at a high level and the second clock signal terminal CLKB changes to a high level.

10 **[0049]** The shifting register further includes the eighth TFT M8. The eighth TFT M8 ensures the first node PU to be kept at a high level so as to continue to charge the capacitor C1 during the period in which the output terminal Output(n) at the present stage is at a high level (i.e., the period during which the shifting register at the present stage is in operation), further improving the turn-on capability of the second TFT M2.

15 **[0050]** In addition, the shifting register further includes the ninth TFT M9 and the tenth TFT M10, and both TFTs are combined with the resetting module 1 so that both the gate and the drain of the second TFT M2 are at a low level upon the second TFT M2 is reset; wherein, the ninth TFT M9 pulls down the first node PU to be at a low level to prevent the second TFT M2 from turning on in error, and the tenth TFT M10 pulls down the output terminal Output(n) at the present stage to be at a low level to prevent the output terminal Output(n) from changing to a high level.

20 **[0051]** It should be noted that, though the shifting register in Fig. 3 includes fourteen TFTs, the embodiments of the disclosure are not limited thereto. For example, a shifting register in accordance with another embodiment of the disclosure can exclude the third TFT M3, and the output terminal Output(n) at the present stage connected to the drain of the second TFT M2 can directly serve as the trigger signal terminal Input(n+1) for the next stage simultaneously.

25 **[0052]** Thus, a shifting register according to another embodiment of the disclosure includes thirteen TFTs, a storage capacitor, and corresponding I/O terminals. The thirteen TFTs are as follows respectively: a first TFT M1, a second TFT M2, a fourth TFT M4, a fifth TFT M5, a sixth TFT M6, a seventh TFT M7, an eighth TFT M8, a ninth TFT M9, a tenth TFT M10, a first resetting TFT T1, a second resetting TFT T2, a third resetting TFT T3, and a fourth resetting TFT T4. The storage capacitor is shown as a capacitor C1. The I/O terminals includes: a trigger signal terminal Input(n) for receiving the trigger signal from the shifting register at the previous stage; an output terminal Output(n) for outputting a level signal for the shifting register at the present stage and for sending a trigger signal to the shifting register at the next stage; a feedback signal terminal Reset(n+1) for receiving a feedback signal from the shifting register at the next stage; a low level signal terminal Vss, and clock signal terminals, wherein the clock signal terminals include a first clock signal terminal CLK and a second clock signal terminal

CLKB, and a clock signal at the first clock signal terminal CLK and that at the second clock signal terminal CLKB have the same frequency and duty cycle, but only differ in phase by 180°. The operations on the thirteen TFTs are the same as those on the corresponding TFTs of the embodiment as described with reference to Fig. 3, and the details are omitted.

[0053] In practice, the TFTs in the embodiments of the disclosure can be of the type of hydrogenated amorphous TFTs, but can be of other types of TFTs.

[0054] Hereinafter, the operation process of the shifting register in the embodiment is described by combining the shifting register shown in Fig.3 with the control timing chart shown in Fig. 4.

[0055] As illustrated in Fig. 4, it is the control timing chart for the shifting register in the embodiment, and there are four phases, i.e., t1, t2, t3 and t4 in the chart. The first clock signal terminal CLK and the second clock signal terminal CLKB alternate in use. STV denotes a switching signal terminal, i.e., the trigger signal terminal Input(n) at the present stage, for receiving a high level signal from the shifting register at the previous stage, wherein a high level signal is denoted by 1, and a low level signal is denoted by 0. Throughout Figs. 5-8, an arrow "↓" represents that the corresponding TFT is ON, and a cross "X" represents that the corresponding TFT is OFF.

[0056] In the phase t1, Input(n)=1, CLK=0, CLKB=1, and Reset(n+1)=0.

[0057] The signal at STV of the shifting register at the present stage is provided by the trigger signal terminal Input(n) at the present stage. As shown in Fig.5, as Input(n)=1, the first TFT M1 turns on and controls the shifting register at the present stage to start operation, and the storage capacitor C1 is charged via the first TFT M1 by a signal at the trigger signal terminal Input(n). As CLKB=1, the seventh TFT M7 turns on, the charging process of the storage capacitor C1 is accelerated via the seventh TFT M7 by a signal at the second clock signal terminal CLKB. At this time, the first node PU is pulled up and is at a high level, and the second TFT M2 turns on; since CLK=0, a low level signal at the first clock signal terminal CLK is output to the output terminal Output(n) at the present stage via the second TFT M2, and the low level signal causes the gate line corresponding to the shifting register at the present stage to be at a low level. Furthermore, since CLKB=1, the sixth TFT M6 turns on. The sixth TFT M6 pulls down the second node PL to a low level Vss when the shifting register at the present stage is not in operation, which prevents the output terminal Output(n) from changing to a high level under the influence of other interference signals. Additionally, since the first node PU is pulled up to a high level, the third TFT M3 turns on, and since the first clock signal terminal CLK=0, the trigger signal terminal Input(n+1) for the next stage is pulled down to a low level, that is, the shifting register at the present stage does not send a trigger signal to the shifting register at the next stage in the phase t1. It can be known from the above, the phase t1 is a

phase during which the storage capacitor C1 is charged.

[0058] In the phase t2, Input(n)=0, CLK=1, CLKB=0, and Reset(n+1)=0.

[0059] As shown in Fig. 6, as Input(n)=0, CLKB=0, the first TFT M1 and the seventh TFT M7 turn off, and the storage capacitor C1 is no more charged via the trigger signal terminal Input(n) and the second clock signal terminal CLKB. As CLKB=0, the sixth TFT M6 turns off, and the sixth TFT M6 will not pull down the second node PL. As CLK=1, after the second TFT M2 turns on under the action of the storage capacitor C1, it outputs a high level at the first clock signal terminal CLK to the output terminal Output(n) at the present stage, and then the output terminal Output(n) at the present stage outputs the high level to the gate line corresponding to the shifting register at the present stage, turning on all the TFTs located in the row corresponding to the gate line, and the data lines begin to write signals. Since CLK=1, the eighth TFT M8 turns on and feeds back the high level at the output terminal Output(n) to the first node PU, to ensure the first node PU to be kept at a high level to continue to charge the capacitor C1, further improving the turn-on capability of the second TFT M2. After Output(n)=1, the second node PL is pulled up, and thus the first resetting TFT T1 and the second resetting TFT T2 turn on. In addition, since CLKB=1, the third resetting TFT T3 turns on, and the first resetting TFT T1 can keep the gate of the fourth resetting TFT T4 at a low level by designing the width-to-length ratio of the channel of the first resetting TFT T1 and that of the third resetting TFT T3 appropriately. Moreover, the second resetting TFT T2 keeps the drain of the fourth resetting TFT T4 at a low level. Since the fourth resetting TFT T4 turns off, the ninth and tenth TFTs M9, M10 turn off, to ensure the first node PU and the output terminal Output(n) at the present stage at a high level continuously and not being pulled down. At this time, the third TFT M3 turns on, under the action of the storage capacitor C1, to allow the trigger signal terminal Input(n+1) for the next stage to change to a high level so as to send a trigger signal to the shifting register at the next stage. In summary, the phase t2 is the phase during which a high level is output to the output terminal Output(n) of the shifting register at the present stage.

[0060] In the phase t3, Input(n)=0, CLK=0, CLKB=1, and Reset(n+1)=1.

[0061] The Reset signal of the shifting register at the present stage is provided from the feedback signal terminal Reset(n+1). As shown in Fig.7, since Reset(n+1)=1, the fourth TFT M4 and the fifth TFT M5 turn on, the output terminal Output(n) is pulled down to Vss after the fourth TFT M4 turns on, and the first node PU is pulled down to Vss after the fifth TFT M5 turns on, so as to avoid the occurrence of the following case: the output terminal Output(n) at the present stage changes to a high level under the influence of the other interference signals, and thus causes the gate line under the control thereof to be switched on under the action of a high level, finally resulting in the switching-on of the gate line in error.

Furthermore, since $CLKB=1$, the sixth TFT M6 turns on, and it pulls the second node PL down to V_{ss} when the shifting register at the present stage is not in operation, to prevent the output terminal Output(n) at the present stage from changing to a high level under the influence of the other interference signals. In summary, the phase t3 is the phase during which a high level is output to the output terminal Output(n+1) of the shifting register at the next stage.

[0062] In the phase t4, $Input(n)=0$, $CLK=1$, $CLKB=0$, and $Reset(n+1)=0$.

[0063] As shown in Fig.8, since $CLK=1$, the third resetting TFT T3 turns on, which causes the gate of the fourth resetting TFT T4 to change to a high level, and thus the fourth resetting TFT T4 turns on. In addition, since the fourth resetting TFT T4 turns on, the gate of the ninth TFT M9 and that of the tenth TFT M10 change to a high level, and thus the ninth and the tenth TFTs M9, M10 turn on. The ninth TFT M9 pulls the first node PU down to V_{ss} , and the tenth TFT M10 pulls the output terminal Output(n) down to V_{ss} , so that both the gate and the drain of the second TFT M2 are at a low level when the second TFT M2 is reset. At this time, for the second TFT M2 with the source to which a high level being applied and the gate to which a low level being applied, the electrons accumulated on the gate insulation layer of the second TFT M2 can pass the potential barrier to arrive at the source of the second TFT M2, and thus the threshold voltage shifting thereof is decreased. In summary, the phase t4 is the phase during which the resetting module 1 resets the second TFT M2, i.e., the resetting phase of the shifting register at the present stage.

[0064] It can be known from the above descriptions, the shifting register in the embodiment can decrease the threshold voltage shifting of the TFTs in the shifting register corresponding to each of the gate lines, and finally it enables the shifting register circuit to operate normally, improving the stability of the shifting register in operation and extending the lifespan of the shifting register.

[0065] For the same reasons, the above operation process can be also applied to the embodiment in which the third TFT M3 is excluded, and the details are omitted.

[0066] Moreover, another embodiment of the disclosure also provides a gate line driving apparatus. As shown in Fig.9, the gate line driving apparatus includes a plurality of shifting registers connected in series, and for the sake of simplicity, it is only shown five shifting registers in Fig. 9, i.e., the (N-2)th shifting register, the (N-1)th shifting register, the Nth shifting register, the (N+1)th shifting register, and the (N+2)th shifting register, respectively. The output terminal Output(n) of the Nth shifting register not only feeds back a feedback signal to the (N-1)th shifting register to switch off the (N-1)th shifting register, but also outputs a trigger signal to the (N+1)th shifting register for triggering the (N+1)th shifting register.

[0067] Beside this, as shown in Fig.9, for the shifting register at individual stages, the clock signal CLK and the clock signal CLKB alternate in use. In particular, it is

illustrated that the clock signal terminal of the Nth shifting register receives the clock signal CLK, and that the clock signal terminals of the (N-1)th and (N+1)th shifting registers receive the clock signal CLKB. Therefore, the clock signal for the Nth shifting register and those for the (N-1)th and (N+1)th shifting registers have totally inverted phases, that is, differ in phase by 180°.

[0068] In another case, that is, the case that the clock signal terminals includes a first clock signal terminal and a second clock signal terminal, for the shifting registers at individual stages, the clock signal CLK and the clock signal CLKB also alternate in use. For the Nth shifting register, its first clock signal terminal receives the clock signal CLK and its second clock signal terminal receives the clock signal CLKB, while for the (N-1)th shifting register and the (N+1)th shifting register, their first clock signal terminal receives the clock signal CLKB, and their second clock signal terminal receives the clock signal CLK.

[0069] As shown in Fig.2, the shifting register at each stage includes three TFTs, a storage capacitor, a resetting module, a feedback receiving module, and corresponding I/O terminals. In particular, the shifting register includes:

[0070] a first TFT M1, having a gate and a source connected together and further connected to the trigger signal terminal Input(n) at the present stage, and a drain connected to a first node PU as a pull-up node, for controlling the shifting register to start operation upon receiving a high level signal sent from the trigger signal terminal Input(n), wherein the trigger signal terminal Input(n) receives a high level signal when an output terminal Output(n-1) of the shifting register at the previous stage (i.e., the shifting register at the (n-1)th stage) outputs a high level; a second thin film transistor M2, having a gate connected to the first node PU, a source connected to a clock signal terminal, and a drain connected to the output terminal Output(n) at the present stage, for providing a high level to the output terminal Output(n) to drive a gate line corresponding to the shifting register at the present stage (i.e., the shifting register at the nth stage) to be switched on; a third TFT M3, having a gate connected to the first node PU, a source connected to the clock signal terminal, and a drain connected to the trigger signal terminal Input(n+1) for the next stage, for providing a trigger signal for the shifting register at the next stage (i.e., the shifting register at the (N+1)th stage) to control the same to start operation; a capacitor C1, being connected between the first node PU and the output terminal Output(n) at the present stage; a resetting module 1, being connected between a second node PL as a pull-down node, the clock signal terminal and a low level signal terminal V_{ss} , for applying a high level to the source of the second TFT M2 and a low level to the gate thereof after the output of the present stage is completed; and a feedback receiving module 2, being connected between the first node PU, the low level signal terminal V_{ss} and the output terminal Output(n) at the present stage, and being further con-

nected to the feedback signal terminal Reset(n+1), for receiving a feedback signal from the next stage to pull down the levels at the first node PU and the output terminal Output(n) at the present stage.

[0071] In addition, for a gate line driving apparatus according to another embodiment of the disclosure, it can be known from the descriptions for Figs. 2-3, that the output terminal Output(n) of the Nth shifting register feeds back a feedback signal to the (N-1)th shifting register (that is, serves as the feedback signal terminal Reset(n-1) at the previous stage) to switch off the (N-1)th shifting register, and at the same time, the trigger signal terminal Input(n+1) of the shifting register at the Nth stage outputs a signal to the (N+1)th shifting register, which serves as a trigger signal for the (N+1)th shifting register.

[0072] As mentioned above, the shifting register at each stage in the gate line driving apparatus in accordance with the another embodiment of the disclosure excludes the third TFT M3, and the output terminal Output(n) at the present stage connected to the drain of the second TFT M2 can directly serve as a trigger signal terminal Input(n+1) for the next stage simultaneously. Besides the exclusion of the third TFT M3, the operation on the shifting register is the same as that of the shifting register in the gate line driving apparatus in the embodiment of the disclosure, and the details are omitted.

[0073] It tends to form and accumulate electrons on the gate insulation layer of a thin film transistor if a voltage is applied to the thin film transistor all the time, and thus it causes the threshold voltage of the thin film transistor to shift. In the gate line driving apparatus according to the embodiments of the disclosure, by applying a high level to the source of the TFT and a low level to the gate thereof, according to the principle of the tunneling effect and the quantum mechanics, the electrons formed and accumulated on the gate insulation layer of the TFT can pass the potential barrier and arrive at the source of the TFT, and thus it decreases the threshold voltage shifting of the TFT in the shifting register corresponding to each gate line, and finally it enables the shifting register circuit to operate normally, improving the stability of the shifting register in operation and extending the lifespan of the shifting register.

[0074] It should be illustrated that the shifting register used in the gate line driving apparatus according to the embodiments has the same function and structure as those of the shifting register used in the embodiments for the shifting register, and thus that they can solve the same technical problem, achieve the same expected effect.

[0075] The disclosure also provides a display device comprising a pixel array and the gate line driving apparatus as described above.

[0076] Although the embodiments of the disclosure are described in the field of liquid crystal display, they can be applied in the field of other display based on pixel array, such as AMOLED (Active Matrix Organic Light Emitting Diode) etc.

[0077] The above descriptions are only for the specific implementations of the disclosure, and the scope of the disclosure are not limited thereto. All the variations or alternations which are easily thought out by those skilled in the art in the light of the present disclosure, should be covered in the scope of the disclosure. Therefore, the protection scope of the disclosure should be defined by the attached claims.

Claims

1. A gate line driving method, comprising the steps of:

decreasing the threshold voltage shifting of a Thin Film Transistor (TFT) in a shifting register corresponding to a gate line;
applying a voltage to a gate of the thin film transistor in the shifting register to turn on the thin film transistor, so that the gate line is provided with a line scan signal to drive the gate line to be switched on.

2. The gate line driving method according to claim 1, wherein, the step for decreasing the threshold voltage shifting of the thin film transistor in the shifting register corresponding to the gate line comprises the step of:

allowing the electrons accumulated at the gate insulation layer of the TFT to arrive at the source of the TFT, so as to decrease the threshold voltage shifting of the TFT.

3. The gate line driving method according to claim 2, wherein, the step for allowing the electrons accumulated at the gate insulation layer of the TFT to arrive at the source of the TFT comprises the step of:

applying a high level to the source of the TFT and a low level to the gate thereof, so that the electrons accumulated at the gate insulation layer of the TFT arrive at the source of the TFT.

4. A shifting register comprising:

a first TFT, having a gate and a source connected together and further connected to a trigger signal terminal at the present stage, and a drain connected to a first node as a pull-up node;
a second TFT, having a gate connected to a first node, a source connected to a clock signal terminal, and a drain connected to an output terminal at the present stage;
a capacitor, being connected between the first node and the output terminal at the present stage;
a resetting module, being connected between a

second node as a pull-down node, the clock signal terminal and a low level signal terminal, for applying a low level to the drain and the gate of the second TFT after the output of the present stage is completed; and
 a feedback receiving module, being connected between the first node, the low level signal terminal and the output terminal of the present stage, and further being connected to a feedback signal terminal, for receiving a feedback signal from the next stage to pull down the first node and the output terminal at the present stage.

- 5. The shifting register according to claim 4, wherein, the resetting module comprises:

a first resetting TFT, having a gate connected to the second node, a source connected to a drain of a third resetting TFT, and a drain connected to the low level signal terminal;
 a second resetting TFT, having a gate connected to the second node, a source connected to a drain of a fourth resetting TFT, and a drain connected to the low level signal terminal;
 the third resetting TFT, having a gate and a source connected to the clock signal terminal, and the drain connected to the source of the first resetting TFT; and
 the fourth resetting TFT, having a gate connected to the drain of the third resetting TFT, a source connected to the clock signal terminal, and the drain connected to the source of the second resetting TFT,
 the shifting register further comprises:

a ninth TFT, having a gate connected to the source of the second resetting TFT in the resetting module, a source connected to the first node, and a drain connected to the low level signal terminal;
 a tenth TFT, having a gate connected to the source of the second resetting TFT in the resetting module, a source connected to the output terminal at the present stage, and a drain connected to the low level signal terminal.

- 6. The shifting register according to claim 4, wherein, the feedback receiving module comprises:

a fourth TFT, having a gate connected to the feedback signal terminal, a source connected to the output terminal at the present stage, and a drain connected to the low level signal terminal;
 and
 a fifth TFT, having a gate connected to the feedback signal terminal, a source connected to the

first node PU, and a drain connected to the low level signal terminal.

- 7. The shifting register according to claim 4, wherein, the shifting register further comprises:

a sixth TFT, having a gate connected to a second clock signal terminal, a source connected to the second node, and a drain connected to the low level signal terminal, wherein a clock signal at the second clock signal terminal and that at the clock signal terminal are inverted each other.

- 8. The shifting register according to claim 4, wherein, the shifting register further comprises:

a seventh TFT, having a gate connected to the second clock signal terminal, a source connected to the trigger signal terminal at the present stage, and a drain connected to the first node, wherein a clock signal at the second clock signal terminal and that at the clock signal terminal are inverted each other.

- 9. The shifting register according to claim 4, wherein, the shifting register further comprises:

an eighth TFT, having a gate connected to the clock signal terminal, a source connected to the first node, and a drain connected to the second node.

- 10. The shifting register according to claim 4, wherein, the shifting register further comprises:

a third TFT, having a gate connected to the first node PU, a source connected to the clock signal terminal, and a drain connected to the trigger signal terminal for the next stage.

- 11. A gate line driving apparatus comprising a plurality of the shifting register according to claims 4-10 connected in series.

- 12. A display device comprising a pixel array and the gate line driving apparatus according to claim 11.

FIG.1

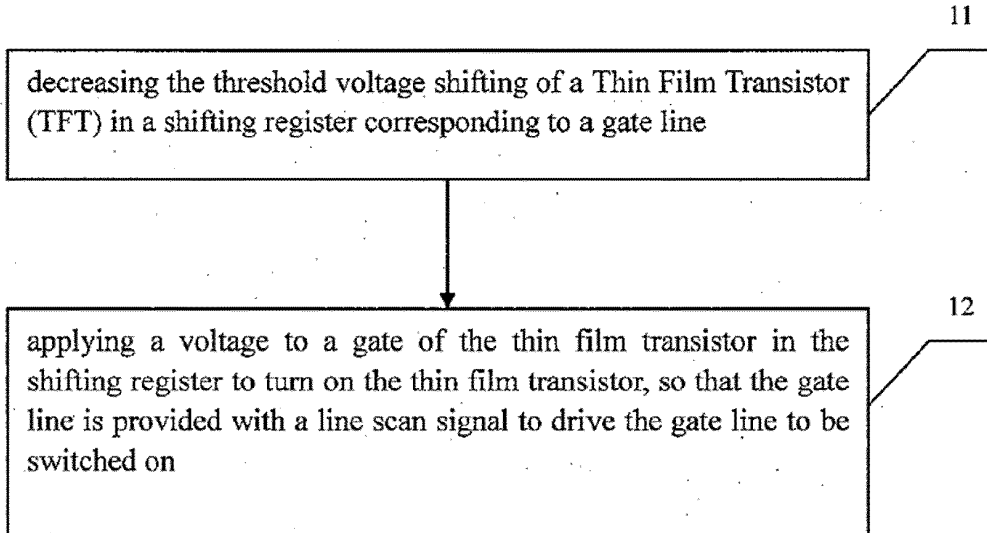


FIG.2

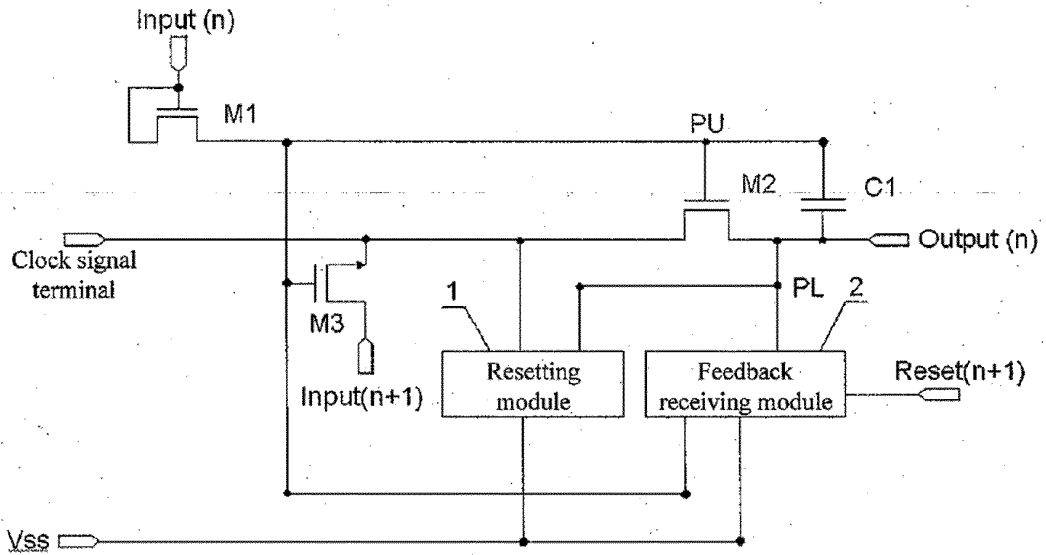


FIG.3

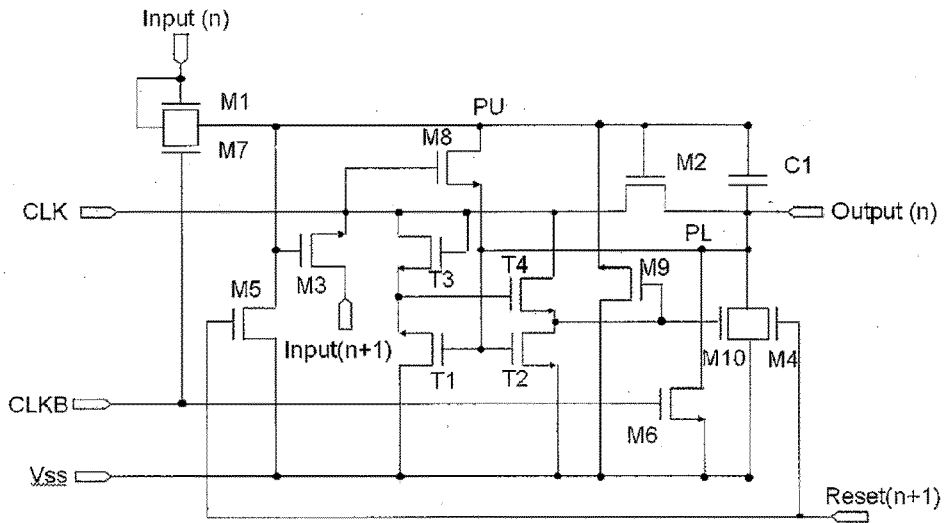


FIG.4

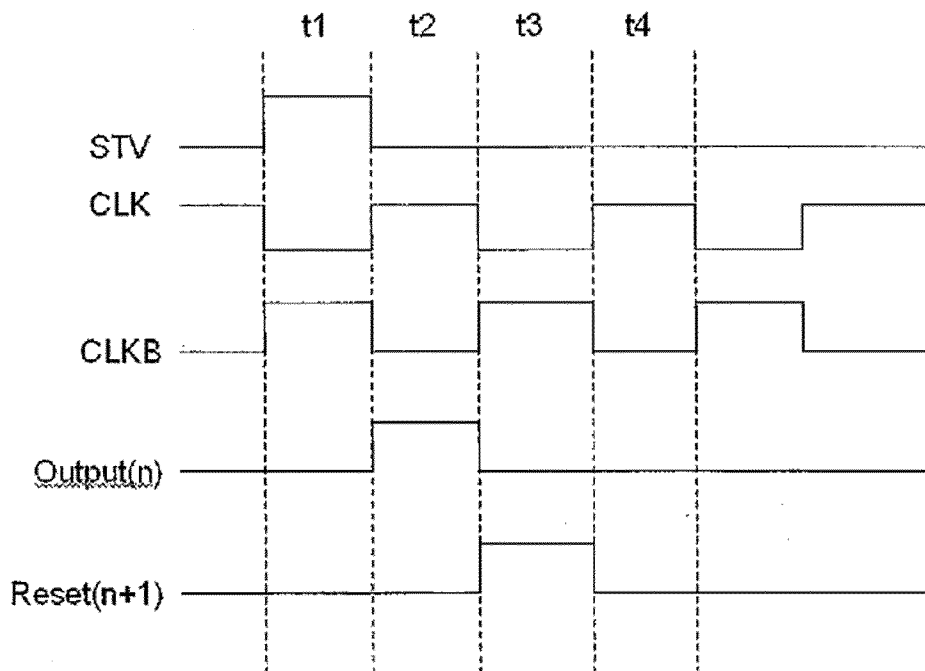


FIG.7

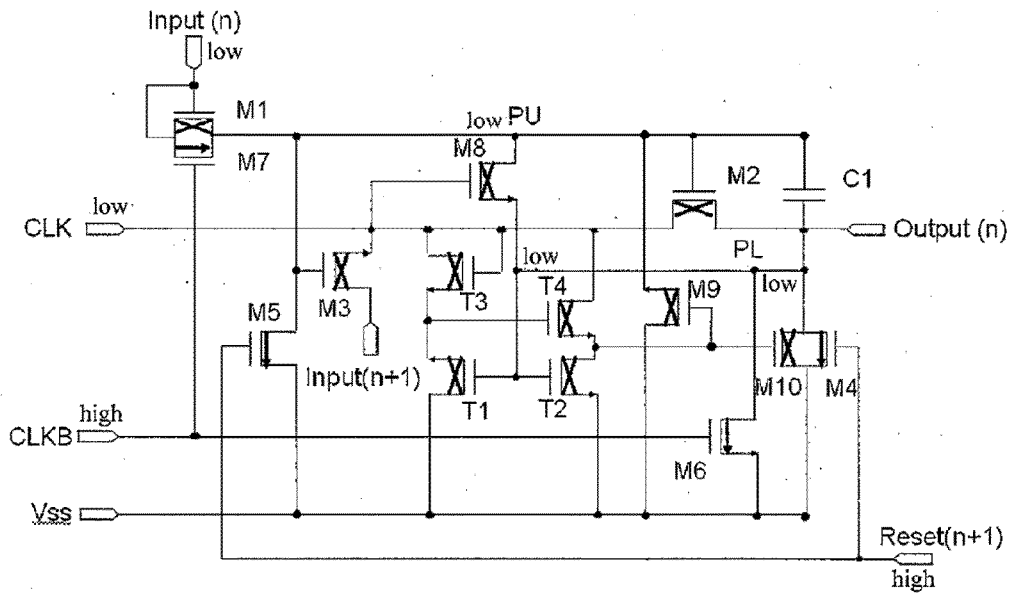


FIG.8

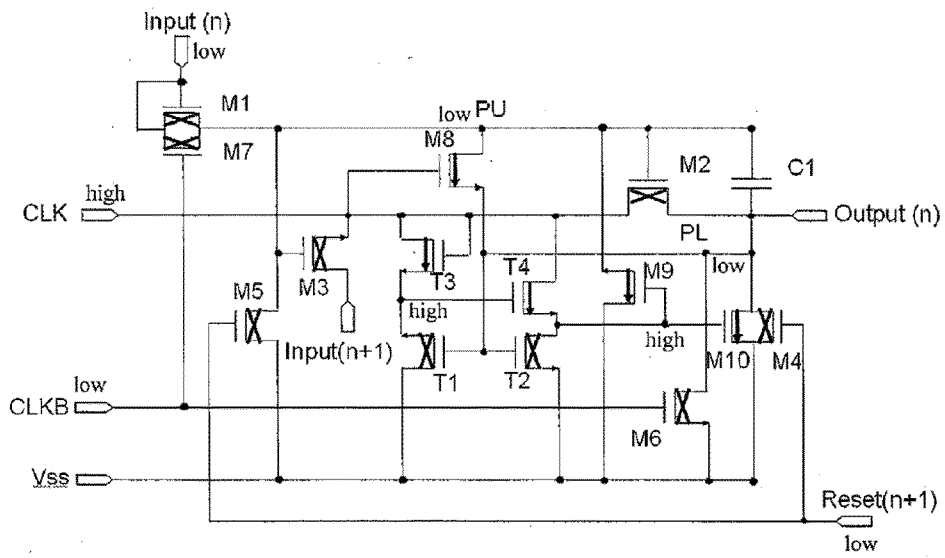
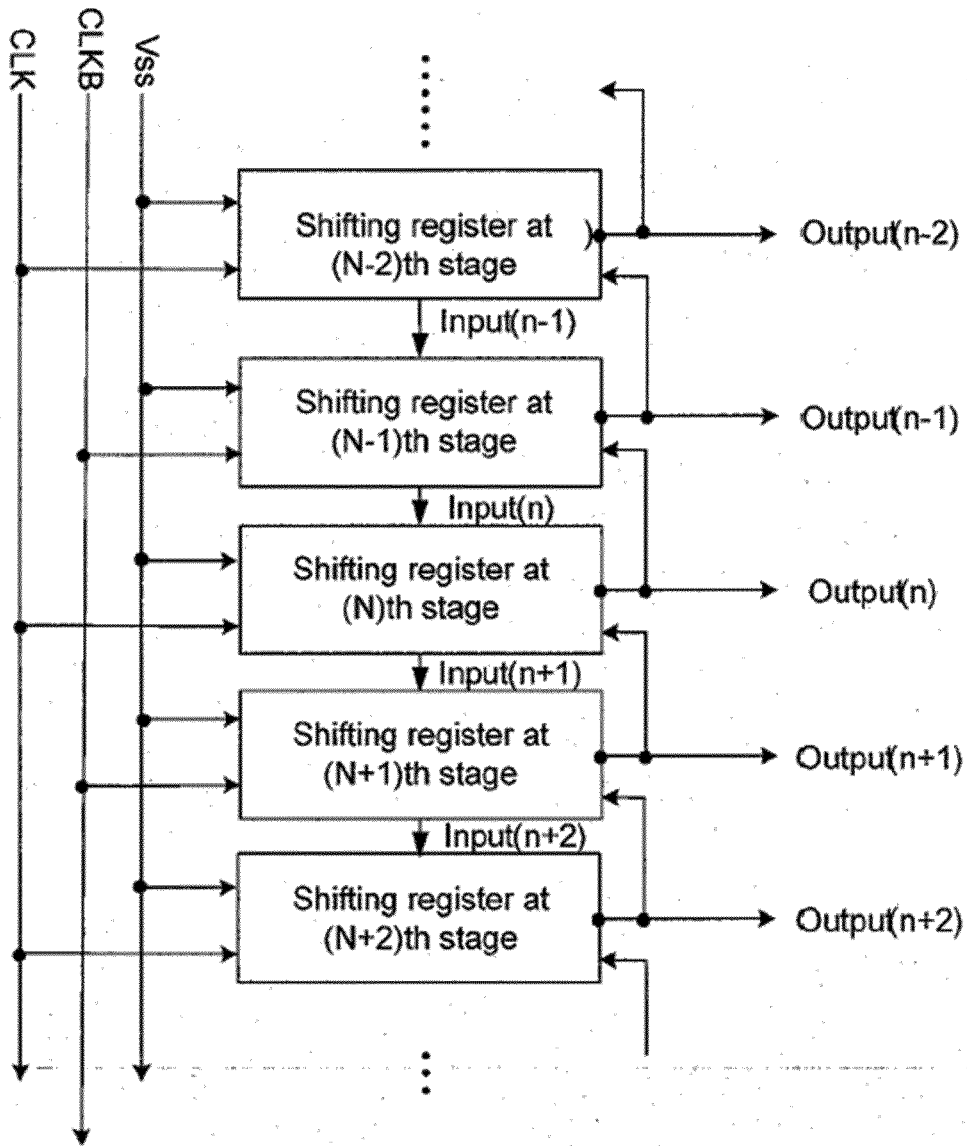


FIG.9



INTERNATIONAL SEARCH REPORT

International application No.

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A. CLASSIFICATION OF SUBJECT MATTER

See the extra sheet

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC: G09G 3/36-; G02F 1/13-

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CNABS, VEN, CNKI: shift w register, flip w flop, step+ w register, circulating w register, transistor, TFT, threshold, voltage, level, potential, source, gate

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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X	CN 101677021 A (BEIJING BOE OPTOELECTRONICS TECHNOLOGY CO., LTD.), 24 March 2010 (24.03.2010)	1-4, 6-9, 11-12
A	CN 102012591 A (BEIJING BOE OPTOELECTRONICS TECHNOLOGY CO., LTD.), 13 April 2011 (13.04.2011), the whole document	1-12
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A	EP 1445862 A2 (SAMSUNG ELECTRONICS CO., LTD.), 11 August 2004 (11.08.2004), the whole document	1-12

 Further documents are listed in the continuation of Box C. See patent family annex.

* Special categories of cited documents:	“T” later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
“A” document defining the general state of the art which is not considered to be of particular relevance	“X” document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
“E” earlier application or patent but published on or after the international filing date	“Y” document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
“L” document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	“&” document member of the same patent family
“O” document referring to an oral disclosure, use, exhibition or other means	
“P” document published prior to the international filing date but later than the priority date claimed	

Date of the actual completion of the international search
18 December 2012 (18.12.2012)Date of mailing of the international search report
17 January 2013 (17.01.2013)Name and mailing address of the ISA/CN:
State Intellectual Property Office of the P. R. China
No. 6, Xitucheng Road, Jimenqiao
Haidian District, Beijing 100088, China
Facsimile No.: (86-10) 62019451

Authorized officer

LUO, Yun

Telephone No.: (86-10) 62085874

INTERNATIONAL SEARCH REPORT
Information on patent family members

International application No.

PCT/CN2012/083558

Patent Documents referred in the Report	Publication Date	Patent Family	Publication Date
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Form PCT/ISA/210 (patent family annex) (July 2009)

INTERNATIONAL SEARCH REPORT

International application No.

PCT/CN2012/083558

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CONTINUATION:

A. CLASSIFICATION OF SUBJECT MATTER

G09G 3/36 (2006.01) i

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G02F 1/13 (2006.01) i

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Form PCT/ISA/210 (extra sheet) (July 2009)

专利名称(译)	光栅线驱动方法，移位寄存器，光栅线驱动装置和显示装置		
公开(公告)号	EP2772902A4	公开(公告)日	2015-04-01
申请号	EP2012790780	申请日	2012-10-26
[标]申请(专利权)人(译)	北京京东方光电科技有限公司		
申请(专利权)人(译)	北京京东方光电科技有限公司.LTD.		
当前申请(专利权)人(译)	北京京东方光电科技有限公司.LTD.		
[标]发明人	CAO KUN HU MING		
发明人	CAO, KUN HU, MING		
IPC分类号	G09G3/36 G02F1/13 G11C19/18		
CPC分类号	G11C19/28 G09G3/3674 G09G2310/0286 G09G2310/08 G09G2320/043		
优先权	201110331772.X 2011-10-26 CN		
其他公开文献	EP2772902B1 EP2772902A1		
外部链接	Espacenet		

摘要(译)

本发明涉及液晶显示领域，公开了一种栅线驱动方法，移位寄存器和栅线驱动装置，用于提高移位寄存器的工作稳定性。栅极线驱动方法包括以下步骤：减小对应于栅极线的移位寄存器中的薄膜晶体管的阈值电压移位；向移位寄存器中的薄膜晶体管的栅极施加电压以导通薄膜晶体管，使得对应于移位寄存器的栅极线提供行扫描信号，以驱动栅极线的行为打开或关闭。移位寄存器包括第一TFT，第二TFT，第三TFT，电容器，复位模块和反馈接收模块。本发明可用于驱动栅极线。